1. General description

Logic level N-channel MOSFET in a small MLPAK33-WF package using Trench12 technology. This product has been designed and qualified to meet AEC-Q101 requirements delivering high performance and endurance.

2. Features and benefits

- Logic-level compatible
- Trench12 MOSFET technology
- Efficient switching with soft body-diode recovery
- Automotive qualified to AEC-Q101 at 175°C
- · Side-wettable flanks for robust solder joints and automatic optical inspection

3. Applications

- LED lighting
- · DC-to-DC conversion
- · Solenoid, motor and other load switching
- · Circuit protection

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	80	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	30	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	41.7	W
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 6.6 A; T_j = 25 °C; Fig. 11		-	17	22	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	I _D = 6.6 A; V _{DS} = 40 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>		-	2.2	-	nC

^{[1] 30} A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.



80 V, 22 mOhm logic level N-channel MOSFET in MLPAK33

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	1 2 3 4	
2	S	source		
3	S	source		D —
4	G	gate		
5	D	drain		G—UTA
6	D	drain		mbb076 S
7	D	drain	8 7 6 5	
8	D	drain	MLPAK33 (SOT8002-3)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK9Q22-80L	MLPAK33	plastic thermal enhanced surface mounted package with side-wettable flanks (SWF); mini leads; 8 terminals;pitch 0.65 mm; 3.3 x 3.3 x 0.8 mm body	SOT8002-3		

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9Q22-80L	7AF

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Tj = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	80	V
V_{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	41.7	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	30	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	21	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 3		-	120	Α
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C
Source-drain	n diode					
I _S	source current	T _{mb} = 25 °C		-	30	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 ^{\circ}C$		-	120	А

80 V, 22 mOhm logic level N-channel MOSFET in MLPAK33

Symbol	Parameter	Conditions		Min	Max	Unit
Avalanche rug	ggedness					
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 17.9 A; $V_{sup} \le 80$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; t_p = 40 μs; Fig. 4	[2] [3]	-	37.8	mJ
I _{AS}	non-repetitive avalanche current	$V_{sup} \le 80 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $R_{GS} = 50 \Omega; Fig. 4$	[2] [3]	-	17.9	A

- [1] 30 A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [3] Refer to application note AN10273 for further information.

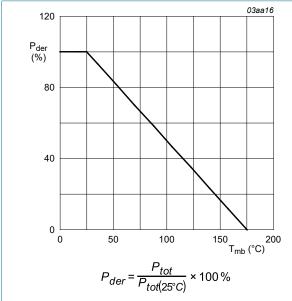


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

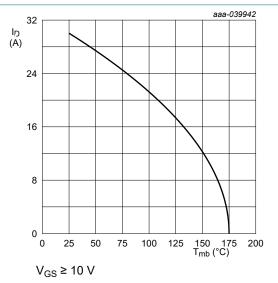
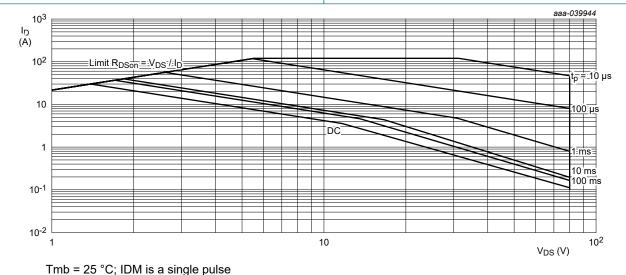


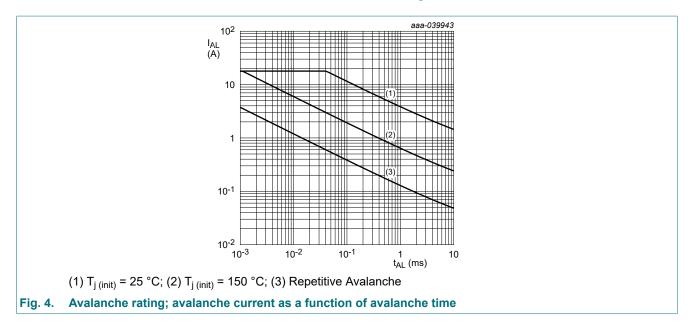
Fig. 2. Continuous drain current as a function of mounting base temperature



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Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

80 V, 22 mOhm logic level N-channel MOSFET in MLPAK33

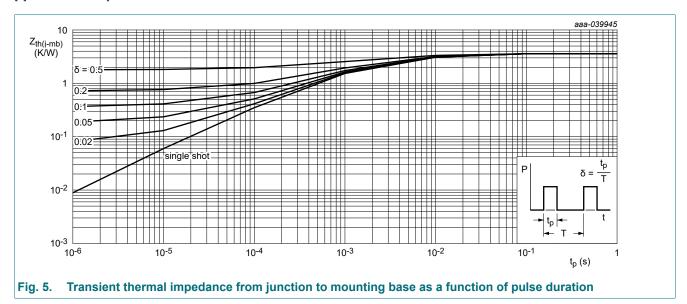


9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5		-	2.4	3.6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		[1]	-	40	-	K/W

[1] Device on 4 layer PCB. Refer to TN00008 for further information.



80 V, 22 mOhm logic level N-channel MOSFET in MLPAK33

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	80	89	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -40 ^{\circ}C$	77	86	-	V
		I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	76	85	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; Fig. 9;$ Fig. 10	1.45	1.7	2.15	V
I _{DSS}	drain leakage current	V _{DS} = 80 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{DS} = 80 V; V _{GS} = 0 V; T _j = 125 °C	-	-	20	μΑ
		V _{DS} = 80 V; V _{GS} = 0 V; T _j = 175 °C	-	-	200	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 6.6 A; T_j = 25 °C; Fig. 11	-	17	22	mΩ
		V_{GS} = 10 V; I_D = 6.6 A; T_j = 105 °C; Fig. 12	-	26	34	mΩ
		V_{GS} = 10 V; I_D = 6.6 A; T_j = 125 °C; Fig. 12	-	27	35	mΩ
		V_{GS} = 10 V; I_D = 6.6 A; T_j = 175 °C; Fig. 12	-	34	46	mΩ
		V_{GS} = 4.5 V; I_D = 5.7 A; T_j = 25 °C; Fig. 11	-	20	30	mΩ
		V_{GS} = 4.5 V; I_D = 5.7 A; T_j = 105 °C; Fig. 12	-	31	43	mΩ
		V_{GS} = 4.5 V; I_D = 5.7 A; T_j = 125 °C; Fig. 12	-	34	48	mΩ
		V_{GS} = 4.5 V; I_D = 5.7 A; T_j = 175 °C; Fig. 12	-	42	62	mΩ
R_G	gate resistance	f = 1 MHz; T _j = 25 °C	-	1.28	-	Ω
Dynamic ch	naracteristics		·	·		
$Q_{G(tot)}$	total gate charge	I _D = 6.6 A; V _{DS} = 40 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	24	36	nC
		I_D = 6.6 A; V_{DS} = 40 V; V_{GS} = 5 V; T_j = 25 °C	-	12	-	nC
Q_{GS}	gate-source charge	$I_D = 6.6 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$	-	4	-	nC
Q_{GD}	gate-drain charge	T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	2.2	-	nC
C _{iss}	input capacitance	V _{DS} = 40 V; V _{GS} = 0 V; f = 1 MHz;	-	1642	=	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	268	-	pF
C _{rss}	reverse transfer capacitance		-	8	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 40 \text{ V}; R_L = 6.1 \Omega; V_{GS} = 10 \text{ V};$	-	4.7	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C$	-	3	-	ns
t _{d(off)}	turn-off delay time	1	-	24	-	ns
t _f	fall time	1	_	7	_	ns

80 V, 22 mOhm logic level N-channel MOSFET in MLPAK33

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drain d	liode					
V _{SD}	source-drain voltage	$I_S = 1.7 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; Fig. 16	-	0.75	1	V
t _{rr}		$I_S = 2.5 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	39	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 40 \text{ V}; T_j = 25 \text{ °C}$	-	19	-	nC

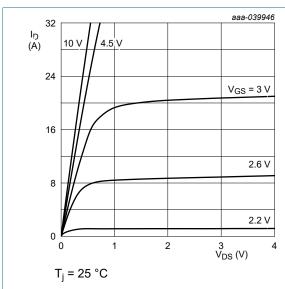


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

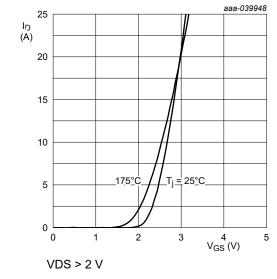


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

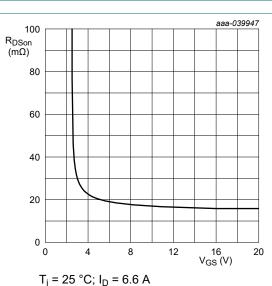
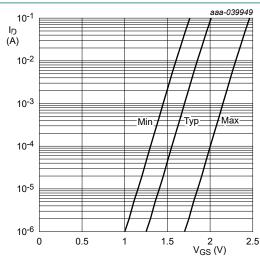


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $T_i = 25 \,^{\circ}C; V_{DS} = 5 \,^{\circ}V$

Fig. 9. Sub-threshold drain current as a function of gate-source voltage

80 V, 22 mOhm logic level N-channel MOSFET in MLPAK33

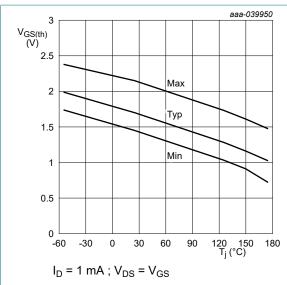


Fig. 10. Gate-source threshold voltage as a function of junction temperature

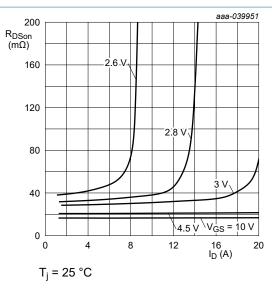


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

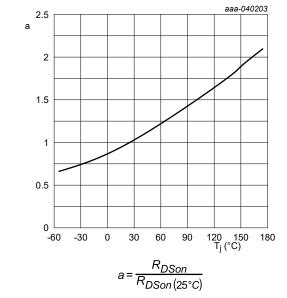
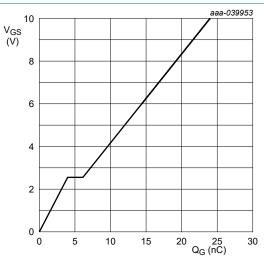


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature



V_{DS} =40V; T_j = 25 °C; I_D = 6.6 A Fig. 13. Gate-source voltage as a function of gate charge; typical values

80 V, 22 mOhm logic level N-channel MOSFET in MLPAK33

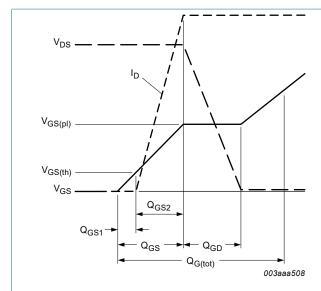
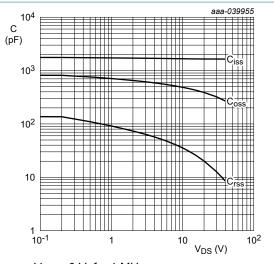


Fig. 14. Gate charge waveform definitions



 $V_{GS} = 0 V$; f = 1 MHz

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

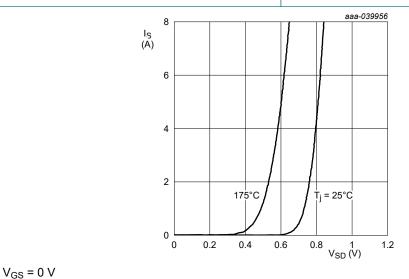
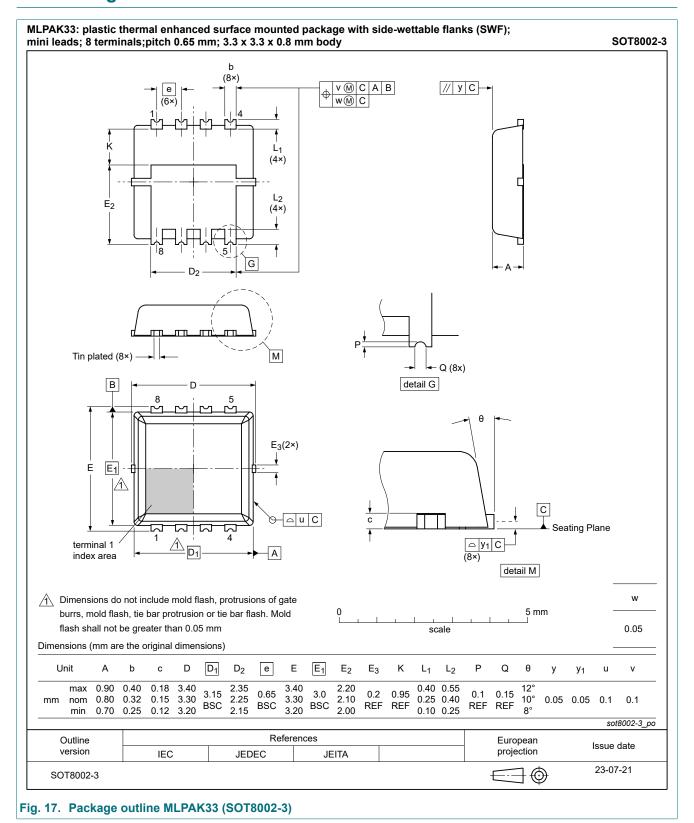


Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

80 V, 22 mOhm logic level N-channel MOSFET in MLPAK33

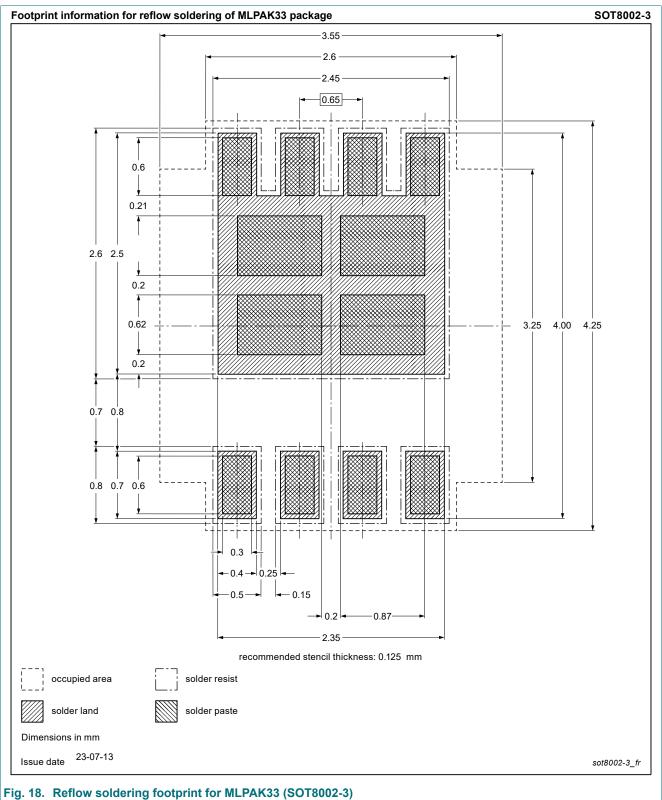
11. Package outline



9 / 12

80 V, 22 mOhm logic level N-channel MOSFET in MLPAK33

12. Soldering



1 ig. 10. Renow soldering lootprint for MEI Artoo (00 10002-0)

80 V, 22 mOhm logic level N-channel MOSFET in MLPAK33

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
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BUK9Q22-80L

80 V, 22 mOhm logic level N-channel MOSFET in MLPAK33

Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	2
9.	Thermal characteristics	4
10	. Characteristics	5
11.	. Package outline	9
12	. Soldering	10
13	. Legal information	11

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